## WHAT IS CLAIMED IS:

A magnetic detecting element comprising:

a multilayer film comprising a first antiferromagnetic layer, a pinned magnetic layer, a nonmagnetic material layer and a free magnetic layer, which are laminated in that order on a substrate; and

a magnetization control layer for controlling magnetization of the free magnetic layer,

magnetic layer extending in the track width direction in contact with the first antiferromagnetic layer, a second magnetic layer facing the first magnetic layer in the thickness direction, and a nonmagnetic intermediate layer interposed between the first and second magnetic layers, the magnetizations of the first and second magnetic layers being antiparallel to each other;

the first antiferromagnetic layer has a predetermined space in the track width direction so that the first antiferromagnetic layer is in contact with both side portions of the first magnetic layer in the thickness direction; and

the electric resistance in the space changes in relation to the magnetization direction of the free magnetic layer and the magnetization direction of the second magnetic layer.

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2. The magnetic detecting element according to claim 1, wherein the multilayer film comprises a free magnetic layer, a nonmagnetic material layer, a pinned magnetic layer and a first antiferromagnetic layer, which are laminated in that order from below, and the magnetization control layer comprises a second antiferromagnetic layer provided below the free magnetic layer to have a predetermined space in the track width direction so that the magnetization control layer is in contact with the bottoms of both side portions of the free magnetic layer, the first antiferromagnetic layer being in contact with the tops of both side portions of the first magnetic layer constituting the pinned magnetic layer.

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3. The magnetic detecting element according to claim 2, wherein the magnetization control layer comprises permanent-magnet layers in direct contact with both side portions of the free magnetic layer.

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- 4. The magnetic detecting element according to claim 2, wherein assuming that the minimum dimension of the space provided in the first antiferromagnetic layer in the track width direction is WP, and the minimum dimension of the space provided in the magnetization control layer in the track width direction is Wf1, Wf1 is the same as or smaller than WP.
- 5. The magnetic detecting element according to claim 1, wherein the multilayer film comprises a free magnetic layer, a nonmagnetic material layer, a pinned magnetic layer and a first antiferromagnetic layer, which are laminated in that order from below, the magnetization control layer comprises permanent-magnet layers provided on both sides of at least

the free magnetic layer and the nonmagnetic layer in the track width direction, the pinned magnetic layer is disposed on the nonmagnetic material layer to partially or entirely extend from the nonmagnetic layer to the permanent-magnet layers, and the first antiferromagnetic layer is provided in contact with the both side portions of the first magnetic layer constituting the pinned magnetic layer.

- 6. The magnetic detecting element according to claim 5,
  wherein both side regions comprising the respective
  permanent-magnet layers are disposed on both sides of at
  least the free magnetic layer and the nonmagnetic material
  layer in the track width direction, and the pinned magnetic
  layer is provided on the nonmagnetic material layer to extend
  from the nonmagnetic material layer to both side regions of
  the element.
- 7. The magnetic detecting element according to claim 5, wherein both side regions comprising the respective

  20 permanent-magnet layers are disposed on both sides of at least the free magnetic layer, the nonmagnetic material layer and the second magnetic layer and nonmagnetic intermediate layer constituting the pinned magnetic layer in the track width direction, and the first magnetic layer constituting

  25 the pinned magnetic layer is provided on the nonmagnetic intermediate layer to extend from the nonmagnetic intermediate layer to both side regions of the element.

- 8. The magnetic detecting element according to claim 5, wherein assuming that the minimum dimension of the space provided in the first antiferromagnetic layer in the track width direction is WP, and the minimum width dimension of the free magnetic layer in the track width direction is Wf2, Wf2 is the same as or smaller than WP.
- 9. The magnetic detecting element according to claim 1, wherein the multilayer film comprises a first

  10 antiferromagnetic layer, a pinned magnetic layer, a nonmagnetic material layer, and a free magnetic layer, which are laminated in that order from below, and the first antiferromagnetic layer is provided with a predetermined space in the track width direction so that the first antiferromagnetic layer is in contact with the bottoms of both side portions of the first magnetic layer in the track width direction.
- 10. The magnetic detecting element according to claim 9,
  20 wherein the substrate provided below the first
  antiferromagnetic layer has recessed portions provided in
  both side portions in the track width direction to have a
  predetermined depth, the first antiferromagnetic layer being
  disposed in the recessed portions with the predetermined
  25 space in the track width direction.
  - 11. The magnetic detecting element according to claim 9, wherein the magnetization control layer comprises a second

antiferromagnetic layer provided on the free magnetic layer to make contact with both side portions of the free magnetic layer and have a predetermined space in the track width direction.

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- 12. The magnetic detecting element according to claim
  11, wherein assuming that the minimum dimension of the space
  provided in the first antiferromagnetic layer in the track
  width direction is WP, and the minimum dimension of the space
  provided in the magnetization control layer in the track
  width direction is Wf3, Wf3 is the same as or smaller than WP.
- 13. The magnetic detecting element according to claim 9, wherein permanent-magnet layers each serving as the

  15 magnetization control layer are provided on both sides of the free magnetic layer in the track width direction so that the bottoms of the permanent-magnet layers are positioned above at least the pinned magnetic layer.
- 14. The magnetic detecting element according to claim
  13, wherein assuming that the minimum dimension of the space
  provided in the first antiferromagnetic layer in the track
  width direction is WP, and the minimum width dimension of the
  free magnetic layer in the track width direction is Wf4, Wf4
  25 is the same as or smaller than WP.
  - 15. The magnetic detecting element according to claim 4, wherein the minimum dimension WP is 0.2  $\mu m$  or less.

16. The magnetic detecting element according to claim 1, further comprising electrode layers provided on both side portions of the multilayer film in such a manner that the direction of a sensing current magnetic field formed by a sensing current flowing from the electrode layers to the multilayer film coincides with the direction of a synthetic magnetic moment per unit area of the magnetic layers constituting the pinned magnetic layer.

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- 17. The magnetic detecting element according to claim 1, further comprising a nonmagnetic metal layer having the same composition as that of the first antiferromagnetic layer and provided in the space to make contact with the first magnetic layer, the nonmagnetic metal layer provided in the space being a disordered crystal structure layer thinner than the first antiferromagnetic layer.
- 18. The magnetic detecting element according to claim
  20 17, wherein the crystal of the first magnetic layer is
  epitaxial or heteroepitaxial with the crystal of the
  nonmagnetic metal layer, the end surface of the pinned
  magnetic layer is open near a surface facing a recording
  medium, and the nonmagnetic metal layer is made of a PtMn
  25 alloy or X-Mn alloy (wherein X is at least one element of Pt,
  Pd, Ir, Rh, Ru, Os, Ni, and Fe).
  - 19. The magnetic detecting element according to claim

18, wherein in the vicinity of the interface with the central portion of the first magnetic layer or over the entire region of the nonmagnetic metal layer, the nonmagnetic metal layer assumes a face-centered cubic lattice (fcc) structure in which an equivalent crystal plane represented by a {111} plane is preferentially oriented in parallel with the interface.

- 20. The magnetic detecting element according to claim

  10 18, wherein the thickness of the nonmagnetic metal layer is 5
  Å to 50 Å.
- 21. The magnetic detecting element according to claim 18, wherein the Pt content of the PtMn alloy or the content 15 of X element in the X-Mn alloy is 55 atomic percent to 95 atomic percent.
- 22. The magnetic detecting element according to claim
  18, wherein in the vicinity of the interface with the
  20 nonmagnetic metal layer or over the entire region of the
  central portion of the first magnetic layer of the pinned
  magnetic layer, at least the central portion facing the
  nonmagnetic metal layer in the thickness direction assumes a
  face-centered cubic lattice (fcc) structure in which an
  25 equivalent crystal plane represented by a {111} plane is
  preferentially oriented in parallel with the interface.
  - 23. The magnetic detecting element according to claim

- 22, wherein the first magnetic layer of the pinned magnetic layer is made of Co or  $Co_xFe_y$  ( $y \le 20$ , x+y = 100).
- 24. The magnetic detecting element according to claim
  5 18, wherein in the vicinity of the interface with the nonmagnetic metal layer or over the entire region of the central portion of the first magnetic layer of the pinned magnetic layer, at least the central portion facing the nonmagnetic metal layer in the thickness direction assumes a
  10 body-centered cubic lattice (bcc) structure in which an equivalent crystal plane represented by a {110} plane is preferentially oriented in parallel with the interface.
- 25. The magnetic detecting element according to claim 15 24, wherein the first magnetic layer of the pinned magnetic layer is made of Co or  $Co_xFe_y$  ( $y \ge 20$ , x+y = 100).
- 26. The magnetic detecting element according to claim
  18, wherein in the vicinity of the interface with the
  20 nonmagnetic metal layer, at least the central portion of the
  first magnetic layer of the pinned magnetic layer facing the
  nonmagnetic metal layer in the thickness direction assumes a
  face-centered cubic lattice (fcc) structure in which an
  equivalent crystal plane represented by a {111} plane is
  25 preferentially oriented in parallel with the interface, and
  in the vicinity of the interface with the nonmagnetic
  intermediate layer, the central portion assumes a bodycentered cubic lattice (bcc) structure in which an equivalent

crystal plane represented by a {110} plane is preferentially oriented in parallel with the interface.

- 27. The magnetic detecting element according to claim
  5 26, wherein the first magnetic layer of the pinned magnetic layer has a composition comprising Co or Co<sub>x</sub>Fe<sub>y</sub> (y ≤ 20, x+y = 100) near the interface with the nonmagnetic metal layer, and the first magnetic layer of the pinned magnetic layer has a composition comprising Co<sub>x</sub>Fe<sub>y</sub> (y ≥ 20, x+y = 100) near the
  10 interface with the nonmagnetic intermediate layer.
  - 28. The magnetic detecting element according to claim 27, wherein the first magnetic layer of the pinned magnetic layer has a Fe concentration gradually increasing in the direction from the interface with the nonmagnetic metal layer to the interface with the nonmagnetic intermediate layer.
- 29. The magnetic detecting element according to claim
  18, wherein a value obtained by dividing the difference
  20 between the distance of nearest neighbor atoms of the
  nonmagnetic metal layer and that of the central portion of
  the first magnetic layer of the pinned magnetic layer in the
  planar direction parallel to the interface by the distance
  between nearest neighbor atoms of the first magnetic layer is
  25 0.05 to 0.20.
  - 30. The magnetic detecting element according to claim 18, wherein the first magnetic layer has a positive

magnetostrictive constant.

31. The magnetic detecting element according to claim 18, further comprising electrode layers made of Cr,  $\alpha$ -Ta or 5 Rh and provided on both sides portions of the magnetic detecting element in the track width direction.